

# 2SA1381/2SC3503

# **High-Definition CRT Display,** Video Output Applications

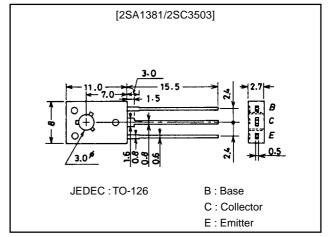
### **Features**

- · High breakdown voltage :  $V_{CEO} \ge 300V$ .
- · Small reverse transfer capacitance and excellent high frequency characteristic
  - : C<sub>re</sub>=1.8 pF (NPN), 2.3pF (PNP), V<sub>CB</sub>=30V.
- · Adoption of MBIT process.

## **Package Dimensions**

unit:mm

2009A



# **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

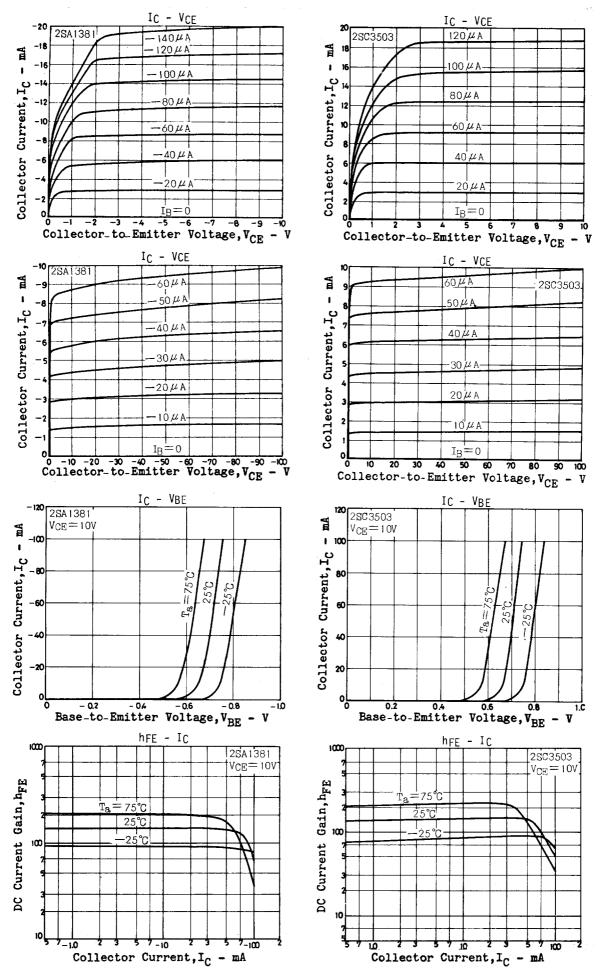
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		(-)300	V
Collector-to-Emitter Voltage	VCEO		(-)300	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		(–)5	V
Collector Current	lC		(-)100	mA
Collector Current (Pulse)	I <sub>CP</sub>		(-)200	mA
Collector Dissipation	PC		1.2	W
		Tc=25°C	7	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

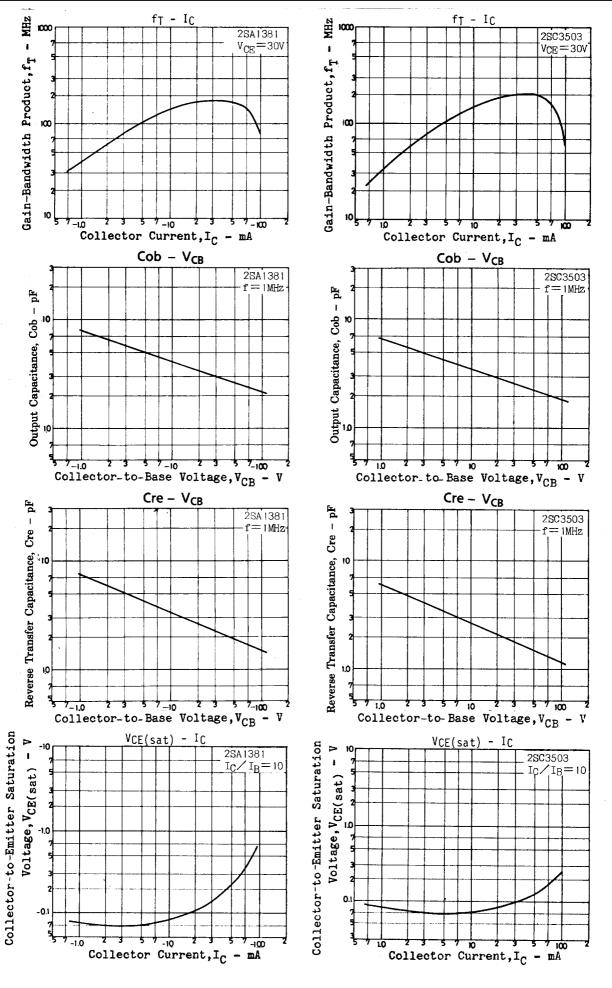
#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Unit		
Farameter	Symbol	Conditions	min	typ	max	Offic
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =(-)200V, I <sub>E</sub> =0			(-)0.1	μA
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB=</sub> (-)4V, I <sub>C</sub> =0			(–)0.1	μA
DC Current Gain	hFE	V <sub>CE</sub> =(-)10V, I <sub>C</sub> =(-)10mA	40*		320*	
Gain-Bandwidth Product	fT	V <sub>CE</sub> =(-)30V, I <sub>C</sub> =(-)10mA		150		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =(-)30V, f=1MHz		2.6		pF
				(3.1)		pF
Reverse Transfer Capacitance	C <sub>re</sub>	V <sub>CB</sub> =(-)30V, f=1MHz		1.8		pF
				(2.3)		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	I <sub>C</sub> =(-)20mA, I <sub>B</sub> =(-)2mA			(-)0.6	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =(-)20mA, I <sub>B</sub> =(-)2mA			(–)1.0	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =(-)10μΑ, I <sub>E</sub> =0	(-)300			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =(-)1mA, R <sub>BE</sub> =∞	(-)300			V
Base-to-Emitter Breakdown Votage	V(BR)EBO	I <sub>E</sub> =(-)10μA, I <sub>C</sub> =0	(–)5			V

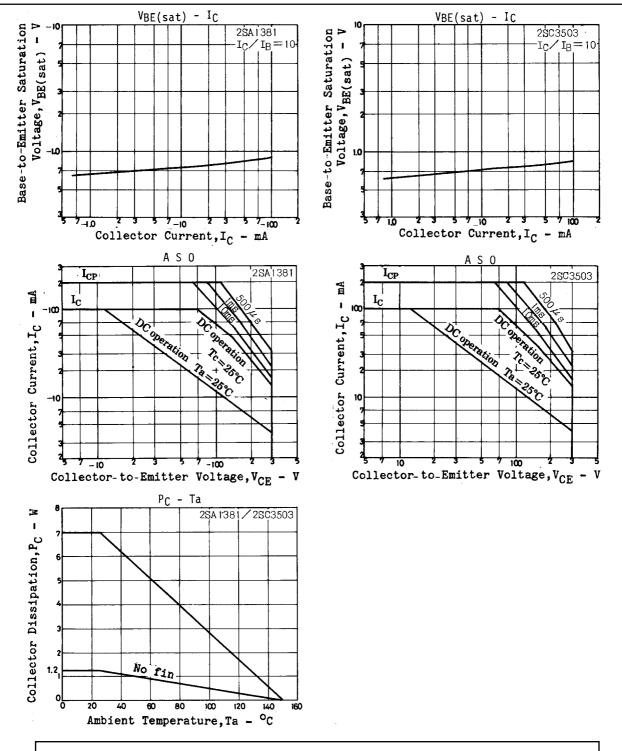
<sup>\*:</sup> The 2SA1381/2SC3503 are classified by 10mA hFE as follows:

40	С	80	60	D	120	100	Е	200	160	F	320





### 2SA1381/2SC3503



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